Ronald Green

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/10695353/publications.pdf

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18	598	1683354 5	2053342 5
papers	citations	h-index	g-index

18	18	18	363
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Time Dependence of Bias-Stress-Induced SiC MOSFET Threshold-Voltage Instability Measurements. IEEE Transactions on Electron Devices, 2008, 55, 1835-1840.	1.6	255
2	Application of reliability test standards to SiC Power MOSFETs. , 2011, , .		57
3	SiC MOSFET threshold-stability issues. Materials Science in Semiconductor Processing, 2018, 78, 32-37.	1.9	49
4	High-Temperature Reliability of SiC Power MOSFETs. Materials Science Forum, 0, 679-680, 599-602.	0.3	43
5	Two-Way Tunneling Model of Oxide Trap Charging and Discharging in SiC MOSFETs. Materials Science Forum, 0, 717-720, 465-468.	0.3	42
6	Temperature-Dependence of SiC MOSFET Threshold-Voltage Instability. Materials Science Forum, 2008, 600-603, 807-810.	0.3	37
7	Measurement considerations for evaluating BTI effects in SiC MOSFETs. Microelectronics Reliability, 2018, 81, 121-126.	0.9	31
8	Comparison of Test Methods for Proper Characterization of <i>V_T</i> in SiC MOSFETs. Materials Science Forum, 0, 858, 833-839.	0.3	19
9	A Study of High Temperature DC and AC Gate Stressing on the Performance and Reliability of Power SiC MOSFETs. Materials Science Forum, 0, 740-742, 549-552.	0.3	14
10	Evaluation of PBTS and NBTS in SiC MOS Using <i>In Situ</i> Charge Pumping Measurements. Materials Science Forum, 0, 740-742, 545-548.	0.3	14
11	Detection of Mobile Ions in the Presence of Charge Trapping in SiC MOS Devices. Materials Science Forum, 0, 717-720, 461-464.	0.3	10
12	Feasibility of SiC Threshold Voltage Drift Characterization for Reliability Assessment in Production Environments. Materials Science Forum, 2017, 897, 509-512.	0.3	10
13	Bias-Temperature-Stress Response of Commercially-Available SiC Power MOSFETs. Materials Science Forum, 0, 821-823, 677-680.	0.3	6
14	Influence of High-Temperature Bias Stress on Room-Temperature <i>V_T</i> Drift Measurements in SiC Power MOSFETs. Materials Science Forum, 0, 963, 757-762.	0.3	5
15	Radiation-Induced Trapped Charging Effects in SiC Power MOSFETs. Materials Science Forum, 0, 778-780, 533-536.	0.3	4
16	Influences of Bias Interruption and Reapplication on High-Temperature Threshold-Voltage Shifts of SiC DMOSFETs. Materials Science Forum, 0, 924, 743-747.	0.3	2
17	Using triangular voltage sweep to detect mobile ions in silicon carbide MOS. , 2011, , .		0
18	(Invited) Implications for Robust Reliability Testing of Power SiC MOSFETs. ECS Transactions, 2011, 41, 215-224.	0.3	0